#### SILICON (Si) POWER MOSFET A CEBF634



# CEBF634

## 250V 🛦 0.45Ω 🛦 8.1A 🛦 Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy TO263 (D2PAK) package ▲ MSL 3 Super high dense cell density for extremely low R<sub>DS(ON)</sub> High power and current handling capability





RoHS

REACH

#### **MAXIMUM RATINGS**

Parameter ( $T_c$ = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V <sub>DS</sub>	250V
Gate-Source Voltage	V <sub>GS</sub>	±20V
Continuous Drain Current at T <sub>c</sub> = 25°C	Ι <sub>D</sub>	8.1A
Continuous Drain Current at T <sub>c</sub> = 100°C	Ι <sub>D</sub>	5.1A
Pulsed Drain Current Note 1	IDM <sup>Note 4</sup>	32A
Maximum Power Dissipation at T <sub>c</sub> = 25°C	PD	74W
Power Dissipation Derating above 25°C	ΔP <sub>D</sub>	0.59W/°C
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

#### THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R <sub>TH_JC</sub>	1.7°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>th_ja</sub>	62.5°C/W

#### **APPLICATIONS**

E-Bike	Industrial Control	Power over Ethernet	Power Inverter	UPS
50		PoE		

#### **PIN DESCRIPTION**

Circuit Diagram	Outline - Bottom View	Pin No.	Description
G (3) S (2)		1 2 3	Drain Source Gate

CEBF634 ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 1



CET MOS

## **ELECTRICAL CHARACTERISTICS** A T<sub>c</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	250			V
Zero Gate Voltage Drain Current	$V_{DS}$ = 250V, $V_{GS}$ = 0V	I <sub>DSS</sub>			25	μA
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS}$ = -20V, $V_{DS}$ = 0V	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 2						
Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu A$	$V_{GS(th)}$	2		4	V
Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.5A	R <sub>DS(ON)</sub>			0.45	Ω
Forward Transconductance	V <sub>DS</sub> = 50V, I <sub>D</sub> = 5.1A	<b>g</b> FS		4.4		S
Dynamic Characteristics Note 3						
Input Capacitance	$V_{DS}$ = 25V, $V_{GS}$ = 0V, f = 1MHz	C <sub>ISS</sub>		925		pF
Output Capacitance	$V_{DS}$ = 25V, $V_{GS}$ = 0V, f = 1MHz	Coss		95		pF
Reverse Transfer Capacitance	$V_{DS}$ = 25V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		20		pF
Switching Characteristics Note 3						
Turn-On Delay Time	$V_{\text{DD}}$ = 125V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 5.6A, $R_{\text{G}(\text{ext})}$ = 12 $\Omega$	t <sub>D(ON)</sub>		16	32	ns
Turn-On Rise Time	$V_{DD}$ = 125V, $V_{GS}$ = 10V, $I_D$ = 5.6A, $R_{G(ext)}$ = 12 $\Omega$	t <sub>R</sub>		3.5	7	ns
Turn-Off Delay Time	$V_{\text{DD}}$ = 125V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 5.6A, $R_{\text{G}(\text{ext})}$ = 12 $\Omega$	t <sub>D(OFF)</sub>		38	76	ns
Turn-Off Fall Time	$V_{DD}$ = 125V, $V_{GS}$ = 10V, $I_D$ = 5.6A, $R_{G(ext)}$ = 12 $\Omega$	t <sub>F</sub>		4	8	ns
Total Gate Charge	$V_{DS}$ = 200V, $V_{GS}$ = 10V, $I_D$ = 5.6A	Q <sub>G</sub>		18	23	nC
Gate Source Charge	$V_{DS}$ = 200V, $V_{GS}$ = 10V, $I_D$ = 5.6A	Q <sub>GS</sub>		3		nC
Gate Drain Charge	$V_{DS}$ = 200V, $V_{GS}$ = 10V, $I_{D}$ = 5.6A	$\mathbf{Q}_{GD}$		5		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current		I <sub>S</sub>			8.1	А
Drain-Source Diode Forward Voltage <sup>Note 2</sup>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 8.1A	$V_{\text{SD}}$		0.9	1.5	V

#### Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

3: Guaranteed by design, not subject to production testing.

4: Pulse width limited by safe operating area.

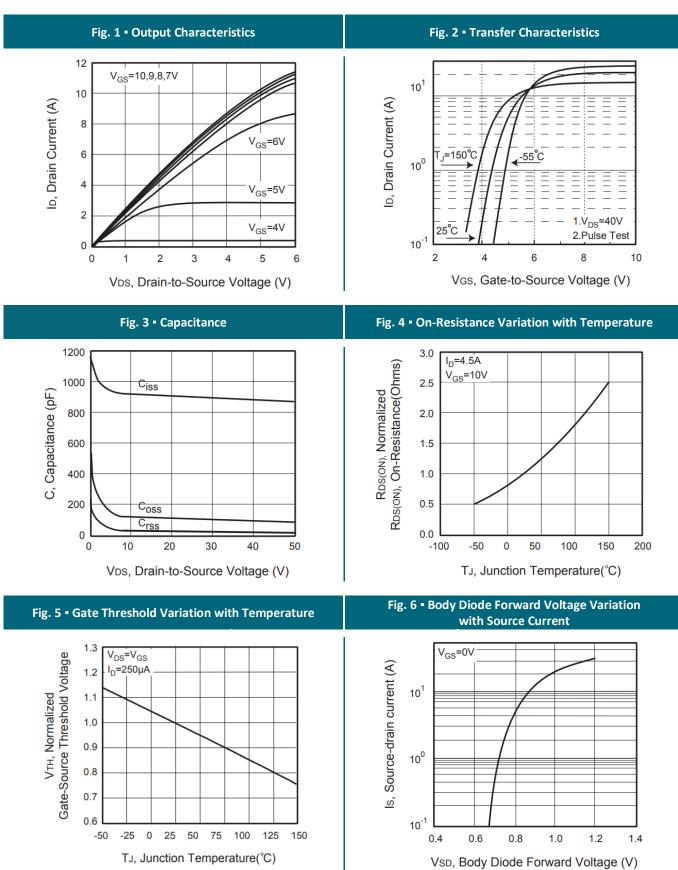
CEBF634 ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 2



MGT **A** Manufacturer Group of Technology

CET MOS

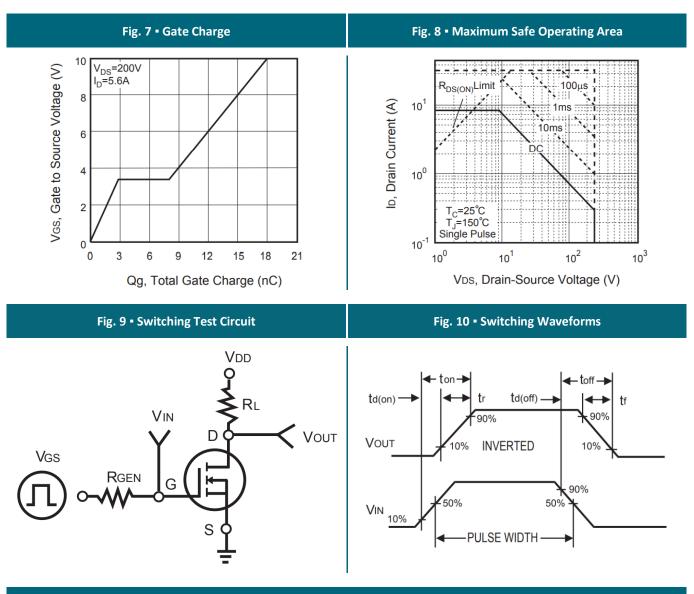
#### **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**



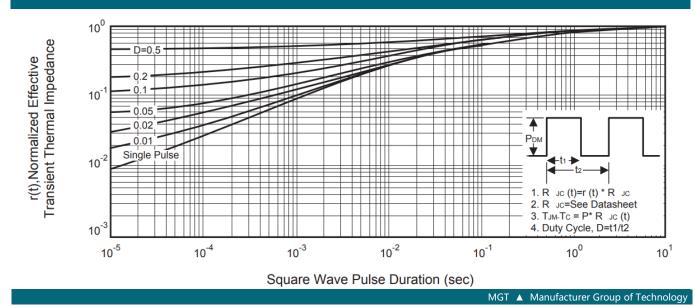


CET MOS

#### **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**



#### Fig. 11 • Normalized Thermal Transient Impedance Curve

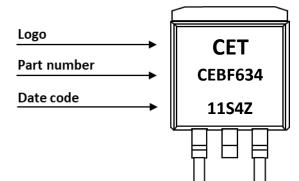


CEBF634 ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 4



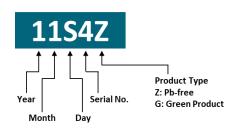






#### DATE CODE

Example: 11S4Z



Coding list for "Day"

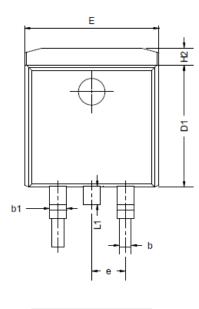
<b>1</b>	<b>2</b>	<b>3</b>	<b>4</b>	<b>5</b>	<b>6</b>	<b>7</b>	<b>8</b>	<b>9</b>	<b>A</b>
01	02	03	04	05	06	07	08	09	10
<b>B</b>	<b>C</b>	<b>D</b>	<b>E</b>	<b>F</b>	<b>G</b>	<b>H</b>	┃	<b>J</b>	<b>K</b>
11	12	13	14	15	16	17	18	19	20
<b>L</b>	<b>M</b>	<b>N</b>	<b>0</b>	<b>P</b>	<b>Q</b>	<b>R</b>	<b>S</b>	<b>T</b>	<b>U</b>
21	22	23	24	25	26	27	28	29	30
<b>V</b> 31									

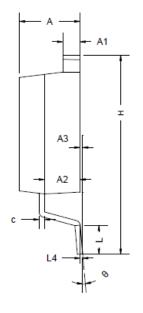
Coding list for "Month"

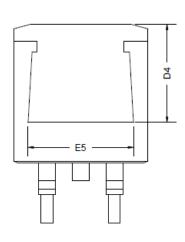
1 Ja		<b>2</b> ⁼eb	<b>3</b> Mar	<b>4</b> Apr	<b>5</b> May	<b>6</b> Jun				
Ju		<b>8</b> Aug	<b>9</b> Sep	<b>A</b> Oct	B Nov	<b>C</b> Dec				
Coding list for "Year"										
	0	1	2	2 3	34					
	2020	202	21 20	22 20	23 202	24				
	5	6	7	<u>۲</u>	39	)				
	2025	202	6 20	27 20	28 20	29				



#### **PACKAGE OUTLINE**







Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	4.37	4.57	4.77	Е	9.86	10.16	10.36
A1	1.22	1.27	1.42	E5	7.06	-	-
A2	2.49	2.69	2.89	е		2.54 BSC	
A3	0.00	0.13	0.25	Н	14.70	15.10	15.50
b	0.70	0.81	0.96	H2	1.07	1.27	1.47
b1	1.17	1.27	1.47	L	2.00	2.30	2.60
С	0.30	0.38	0.53	L1	1.40	1.55	1.70
D1	8.50	8.70	8.90	L4		0.25 BSC	
D4	6.60	-	-	θ	0°	5°	9°

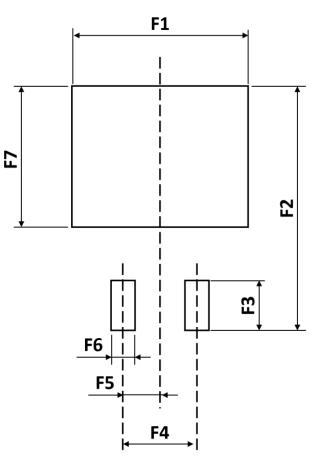
### **ORDERING INFORMATION**

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEBF634	TO263 (D2PAK)	Reel	800pcs	800pcs	6,400pcs



CET MOS

#### **RECOMMENDED PAD LAYOUT**



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	12.20	-	F5	-	2.54	-
F2	-	16.90	-	F6	-	1.60	-
F3	-	2.54	-	F7	-	9.75	-
F4	-	5.08	-				

Notes:

1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

CEBF634 Rev.001 Date: 30/09/2022 Page: 7

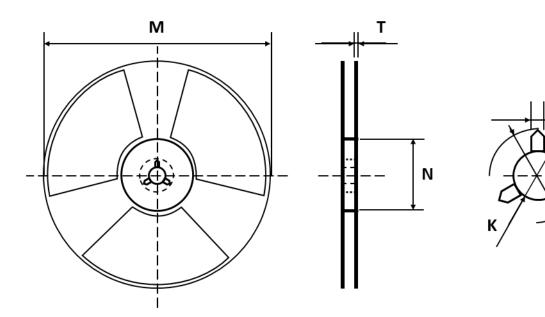


S

Н

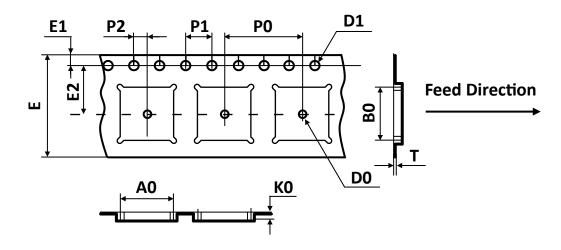


#### **REEL DIMENSIONS** All dimensions in mm



Tape Size	Reel Size	М	N	Т	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
24mm	Ø330	±2.00	±0.50	±0.20	±0.50	+0.50	+0.50
		±2.00	±0.50	±0.20	±0.50	-0.20	-0.20

## TAPE DIMENSIONS All dimensions in mm



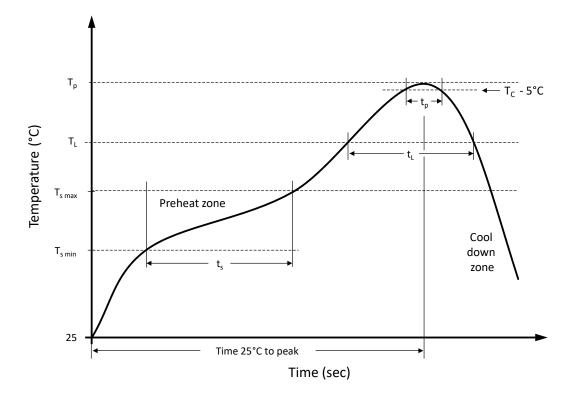
Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	Т
TO263	10.80	16.30	4.85	1.50	1.55	24.00	1.75	11.50	16.00	4.00	2.00	0.35
(D <sup>2</sup> PAK)	±0.10	±0.10	±0.10	±0.10	±0.05	±0.30	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05







#### **RECOMMENDED REFLOW SOLDERING PROFILE**



#### **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time $t_s$ from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time $t_L$ maintained above $T_L$	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate ( $T_L$ to $T_p$ )		max. 6 °C/second max. 6 °C/second	
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



## **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

#### DISCLAIMER

Except for the written expressed warranties, MGT does not implicitly, by assumption or whatever else, warrant, under-take, promise any other warranty or guaranty for any MGT product.

All information and technical specifications made available by MGT are for guidance only and we reserve the right to change or modify them without prior notice. Unless expressly stated in writing by MGT, we reject any guarantees, obligations, or warranties.

All MGT products with the technical specifications described are suitable for use in certain applications. Operating, production, storage and environmental conditions can have a massive influence on the parameters mentioned in the data sheets, which cause the performance to vary over time.

It is subject to the user's duty of care to design and validate his products in such a way that appropriate measures are taken, such as protective circuits or redundant systems to ensure the safety standards required in the application.

MGT components are not designed or rated for use in life support, rescue, safety critical, military, or aerospace applications where failure or malfunction could result in property or environmental damage, serious injury or death. In the aforementioned cases, please contact us before using MGT products.

In principle, we reserve all rights and MGT's general terms and conditions apply. You can find them on our website <u>www.mgt.co.com.</u>